

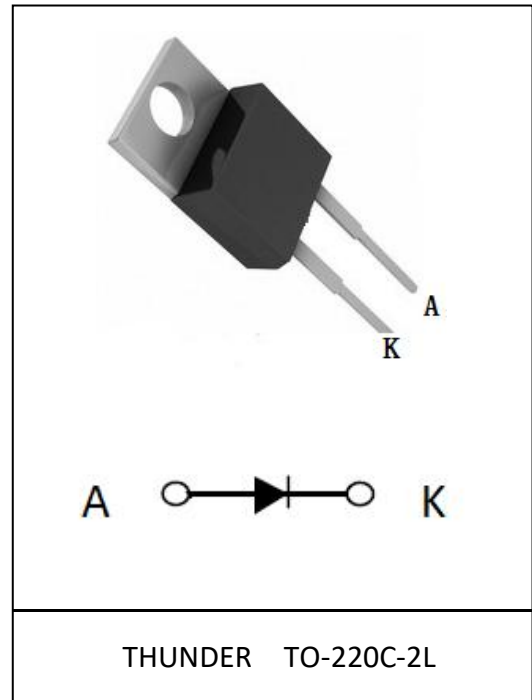
## FRED

### Ultrafast Soft Recovery Diode, 10A

#### Features:

- Ultrafast Recovery
- 175°C operating junction temperature
- High frequency operation
- Low power loss, less RFI and EMI
- Low  $I_R$  value
- High surge capacity
- Epitaxial chip construction

Product Summary	
$V_R$	1200 V
$I_{F(AV)}$	10A
$t_{rr}$	40 ns



#### Description/Applications

These diodes are optimized to less losses and EMI/RFI in high frequency power conditioning system. The soft recovery behavior of the diodes offers the need as snubber in most applications. These devices are ideally suited for HF welding power converters and other applications where the switching losses are not significant portion of the total losses.

#### Absolute Maximum Ratings

Parameter	Symbol	Test Conditions	Values	Units
Repetitive peak reverse voltage	$V_{RRM}$		1200	V
Continuous forward current	$I_{F(AV)}$	$T_c = 110^\circ\text{C}$	10	A
Single pulse forward current	$I_{FSM}$	$T_c = 25^\circ\text{C}$	64	
Maximum repetitive forward current	$I_{FRM}$	Square wave, 20kHz	20	
Operating junction	$T_j$		175	$^\circ\text{C}$
Storage temperatures	$T_{stg}$	-55 to +175		$^\circ\text{C}$

## Electrical characteristics (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ.	Max.	Units
Breakdown voltage Blocking voltage	$V_{BR}$ , $V_R$	$I_R=100\mu A$	1200			V
Forward voltage (Per Diode)	$V_F$	$I_F=10A$		2.10	2.70	
		$I_F=10A$ , $T_j=125^\circ C$		1.95	2.50	
Reverse leakage current(Per Diode)	$I_R$	$V_R=V_{RRM}$			20	$\mu A$
		$T_j=150^\circ C$ , $V_R=1200V$			200	
Reverse recovery time(Per Diode)	$t_{rr}$	$I_F=0.5A$ , $I_R=1A$ , $I_{RR}=0.25A$		40	50	ns
		$I_F=1A$ , $V_R=30V$ , $di/dt=200A/\mu s$		26	36	

## Thermal characteristics

Paramter	Symbol	Typ	Units
$R_{\theta JC}$	Junction-to-Case	2.0	$^\circ C/W$

## Electrical performance (typical)

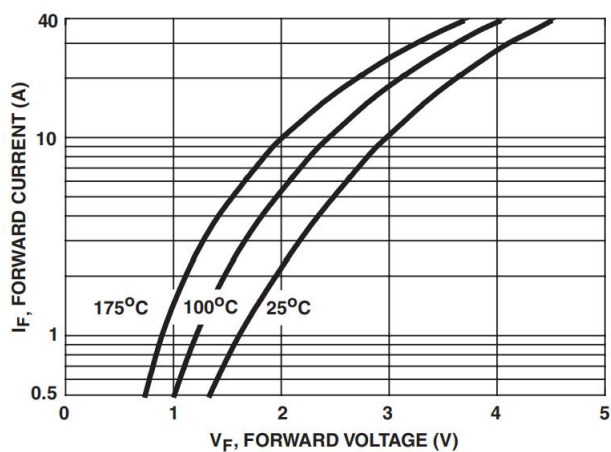


FIGURE 1. FORWARD CURRENT vs FORWARD VOLTAGE

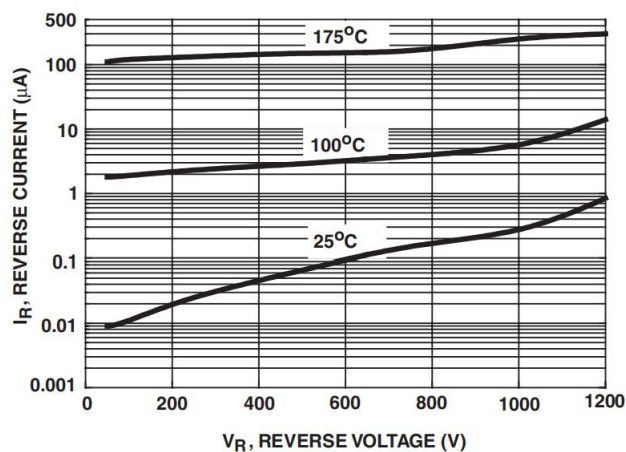


FIGURE 2. REVERSE CURRENT vs REVERSE VOLTAGE

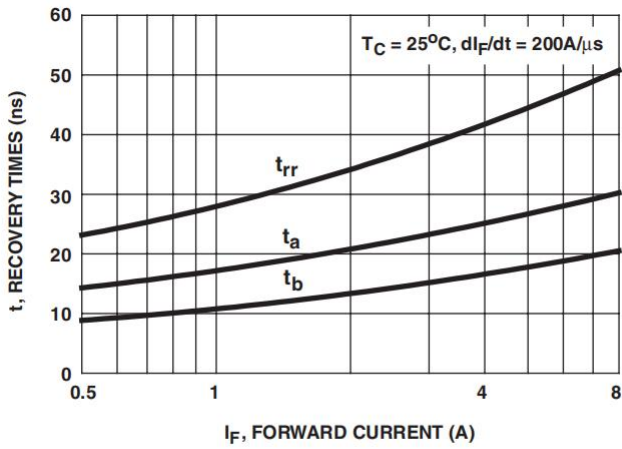


FIGURE 3.  $t_{rr}$ ,  $t_a$  AND  $t_b$  CURVES vs FORWARD CURRENT

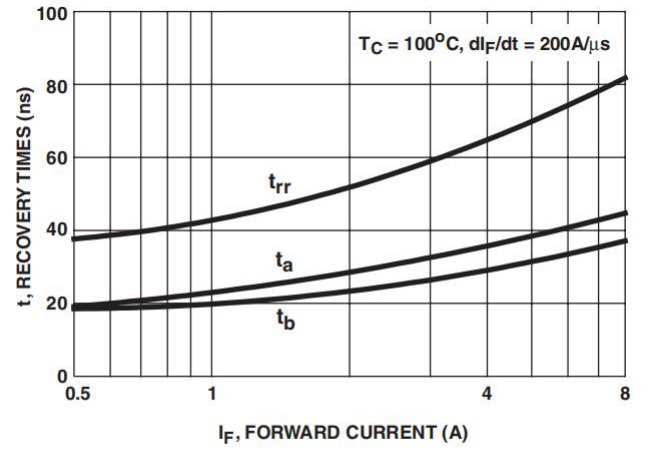


FIGURE 4.  $t_{rr}$ ,  $t_a$  AND  $t_b$  CURVES vs FORWARD CURRENT

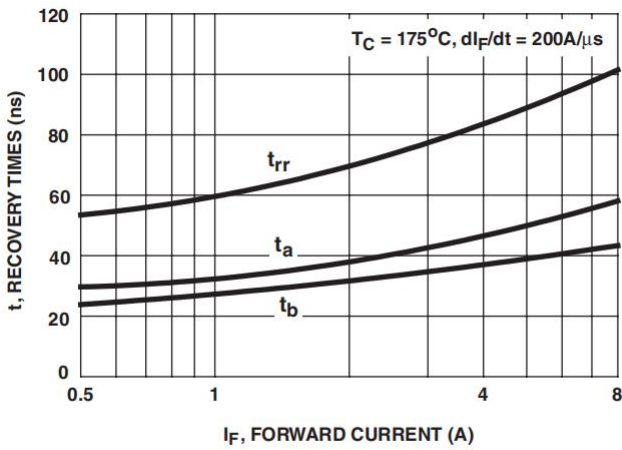


FIGURE 5.  $t_{rr}$ ,  $t_a$  AND  $t_b$  CURVES vs FORWARD CURRENT

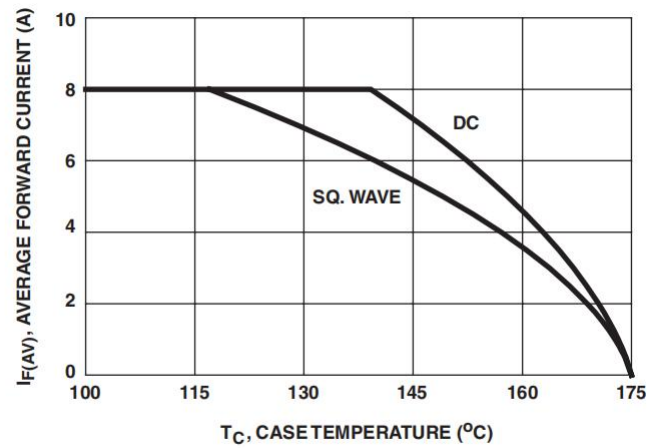


FIGURE 6. CURRENT DERATING CURVE

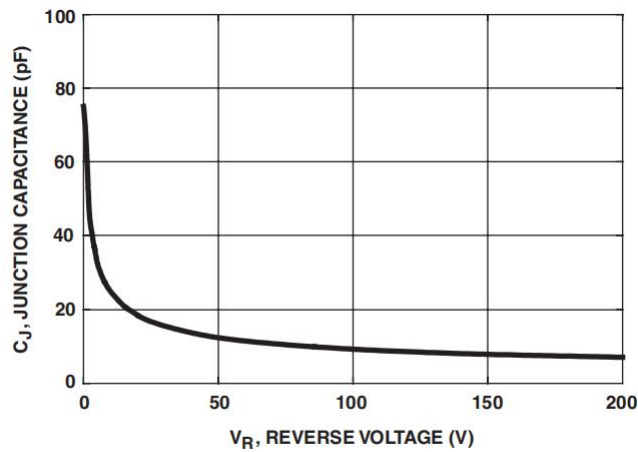
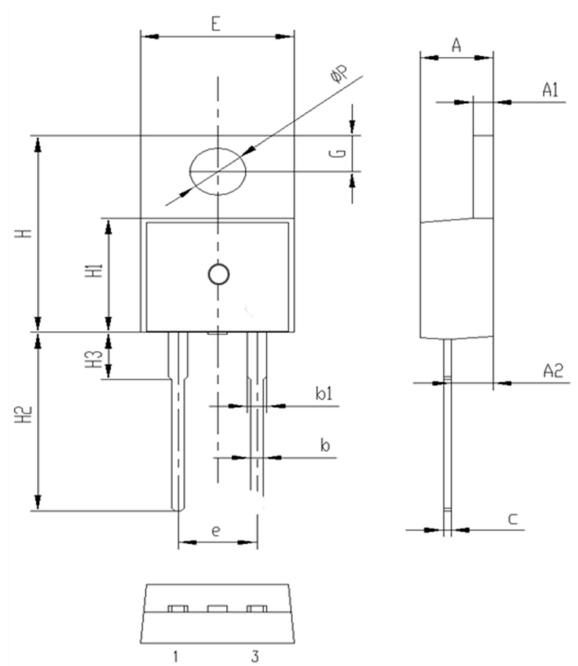


FIGURE 7. JUNCTION CAPACITANCE vs REVERSE VOLTAGE

## Package Information

### TO-220C-2L PACKAGE



Symbol	Dimensions(millimeters)	
	Min.	Max.
A	4.30	4.70
A1	1.17	1.37
A2	2.20	2.60
b	0.60	1.00
b1	1.17	1.37
c	0.40	0.60
e	4.88	5.28
E	9.80	10.2
H	15.5	15.9
H1	9.00	9.40
H2	12.6	13.6
H3	2.80	3.20
G	2.60	3.00
$\Phi P$	3.40	3.80

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### -Headquarters

WuXi Thunder Microelectronics Incorporated Limited

Building E1-9F, No.200 LingHu Road, XinWu district,WuXi,China 214135

Tel:+86-510-85160109

Fax:+86-510-85160109